

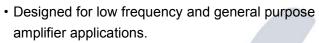


## **isc Silicon NPN Power Transistor**

#### **DESCRIPTION**

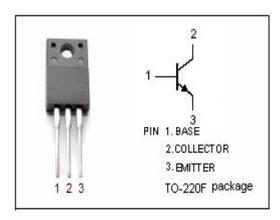
- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 60V(Min)
- · Good Linearity of hFE
- · Wide Area of Safe Operation
- Complement to Type 2SB1133
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

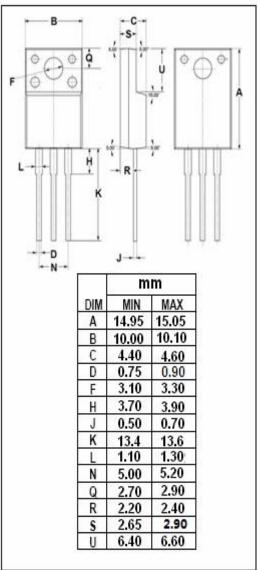




### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
Vceo	Collector-Emitter Voltage	60	V	
V <sub>EBO</sub>	Emitter-Base Voltage	6	V	
lc	Collector Current-Continuous	3	А	
Ісм	Collector Current-Peak	8	Α	
Pc	Collector Power Dissipation @T <sub>a</sub> =25℃	2	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	25		
TJ	Junction Temperature	unction Temperature 150		
T <sub>stg</sub>	Storage Temperature -40~15		$^{\circ}$ C	







### **isc Silicon NPN Power Transistor**

2SD1666

#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
$V_{(\text{BR})\text{CEO}}$	Collector-Emitter Breakdown Voltage	$I_C$ = 5mA ; $R_{BE}$ = $\infty$	60			V		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	60			V		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA ; I <sub>C</sub> = 0	6			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.2A			1.0	V		
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 5V			1.0	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V ; I <sub>E</sub> = 0			100	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			100	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	70		280			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A ; V <sub>CE</sub> = 5V	20					
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f= 1MHz		60		pF		
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A ; V <sub>CE</sub> = 5V		8		MHz		

# ♦ h<sub>FE-1</sub> Classifications

Q	R	s
70-140	100-200	140-280

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